BD159G

Plastic Medium-Power Silicon NPN Transistor

This device is designed for power output stages for television, radio, phonograph and other consumer product applications.

Features

- Suitable for Transformerless, Line-Operated Equipment
- High Power Dissipation Rating for High Reliability
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	350	Vdc
Collector-Base Voltage	V _{CB}	375	Vdc
Emitter-Base Voltage	V _{EB}	5.0	Vdc
Collector Current - Continuous	I _C	0.5	Adc
Collector Current - Peak	I _{CM}	1.0	Adc
Base Current	Ι _Β	0.25	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	20 0.16	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

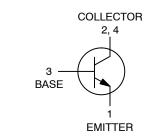
Characteristic	Symbol	Max	Unit	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	6.25	°C/W	



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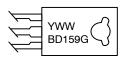
www.onsemi.com

0.5 AMPERE **POWER TRANSISTOR NPN SILICON 350 VOLTS, 20 WATTS**





MARKING DIAGRAM



= Year WW = Work Week BD159 = Device Code = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
BD159G	TO-225 (Pb-Free)	500 Units/Box

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit			
OFF CHARACTERISTICS							
Collector–Emitter Sustaining Voltage (I _C = 1.0 mAdc, I _B = 0)	BV _{CEO}	350	-	Vdc			
Collector Cutoff Current (at rated voltage)	I _{CBO}	-	100	μAdc			
Emitter Cutoff Current (V _{EB} = 5.0 Vdc, I _C = 0)	I _{EBO}	-	100	μAdc			
ON CHARACTERISTICS							
DC Current Gain (I _C = 50 mAdc, V _{CE} = 10 Vdc)	h _{FE}	30	240	-			

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

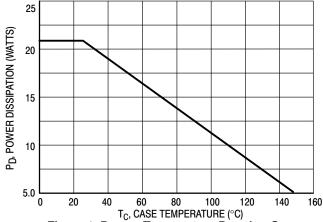
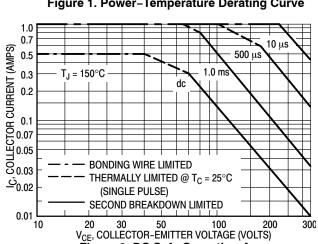
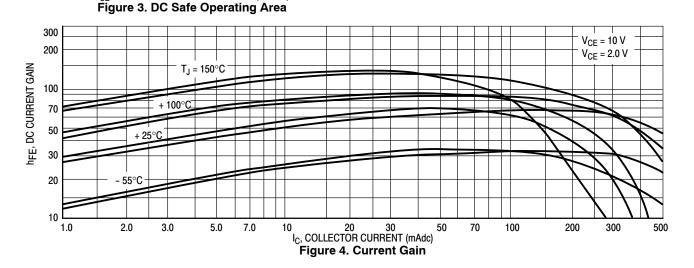


Figure 1. Power-Temperature Derating Curve

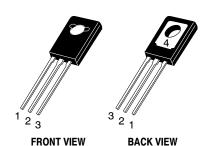


 $V_{BE} @ I_{C}/I_{B} = 10$ 0.8 V, VOLTAGE (VOLTS) V_{BE} @ V_{CE} = 10 V $V_{CE(sat)} @ I_C/I_B = 10$ 0.2 +25°C $I_{C}/I_{B} = 5.0$ 0 30 50 100 I_C, COLLECTOR CURRENT (mA) 20 10 200 300 500 Figure 2. "On" Voltages

The Safe Operating Area Curves indicate I_C - V_{CE} limits below which the device will not enter secondary breakdown. Collector load lines for specific circuits must fall within the applicable Safe Area to avoid causing a catastrophic failure. To insure operation below, the maximum T_J, power-temperature derating must be observed for both steady state and pulse power conditions.



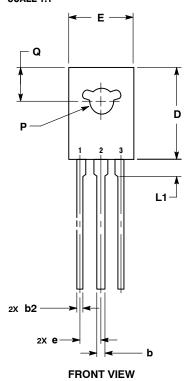


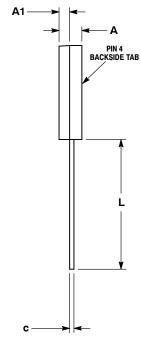


TO-225 CASE 77-09 **ISSUE AD**

DATE 25 MAR 2015

SCALE 1:1





SIDE VIEW

- NOTES:

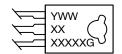
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. NUMBER AND SHAPE OF LUGS OPTIONAL.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.40	3.00			
A1	1.00	1.50			
b	0.60	0.90			
b2	0.51	0.88			
С	0.39	0.63			
D	10.60	11.10			
E	7.40	7.80			
е	2.04 2.54				
L	14.50	16.63			
L1	1.27	2.54			
P	2.90	3.30			
Q	3.80 4.20				

GENERIC MARKING DIAGRAM*



= Year

ww = Work Week

XXXXX = Device Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. 2., 4. 3.	EMITTER COLLECTOR BASE	STYLE 2: PIN 1. 2., 4. 3.	STYLE 3: PIN 1. 2., 4. 3.	BASE COLLECTOR EMITTER	STYLE 4: PIN 1. 2., 4. 3.	ANODE 1 ANODE 2 GATE	2., 4.	MT 1 MT 2 GATE
STYLE 6: PIN 1. 2., 4. 3.	CATHODE GATE ANODE	STYLE 7: PIN 1. 2., 4. 3.	STYLE 8: PIN 1. 2., 4. 3.	SOURCE GATE DRAIN	STYLE 9: PIN 1. 2., 4. 3.	GATE DRAIN SOURCE	STYLE 10: PIN 1. 2., 4. 3.	SOURCE DRAIN

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DESCRIPTION:	TO-225		PAGE 1 OF 1		

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